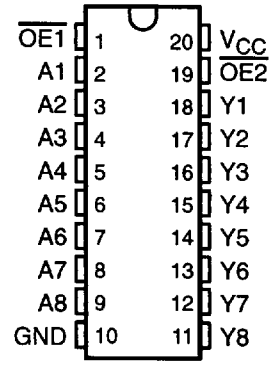
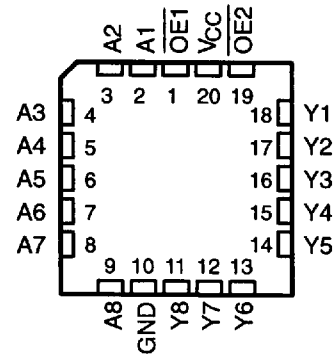
- **State-of-the-Art *EPIC*-IIB™ BiCMOS Design Significantly Reduces Power Dissipation**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Plastic (N) and Ceramic (J) 300-mil DIPs**

SN54ABT541B . . . J OR W PACKAGE
SN74ABT541B . . . DB, DW, N, OR PW PACKAGE
(TOP VIEW)



SN54ABT541B . . . FK PACKAGE
(TOP VIEW)



description

The 'ABT541B octal buffers and line drivers are ideal for driving bus lines or buffering memory address registers. The devices feature inputs and outputs on opposite sides of the package to facilitate printed-circuit-board layout.

The 3-state control gate is a two-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all eight outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor. The minimum value of the resistor is determined by the current-sinking capability of the driver.

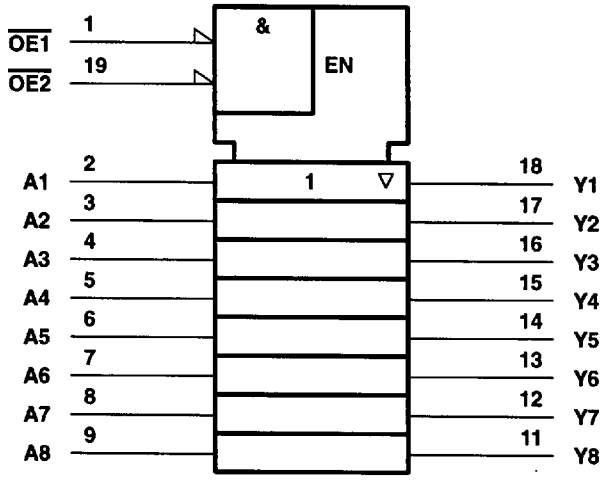
The SN74ABT541B is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54ABT541B is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT541B is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

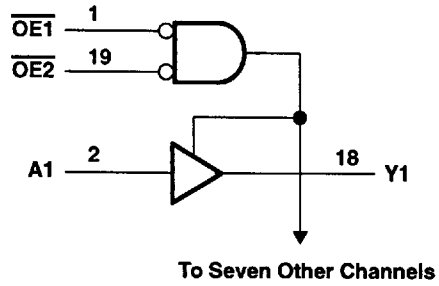
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 7 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O ..... –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABT541B ..... 96 mA
SN74ABT541B ..... 128 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... –18 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... –50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DB package ..... 0.6 W
DW package ..... 1.6 W
N package ..... 1.3 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and negative-output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the N package, which has a trace length of zero. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*.

recommended operating conditions (see Note 3)

		SN54ABT541B		SN74ABT541B		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
I_{OH}	High-level output current		–24		–32	mA
I_{OL}	Low-level output current		48		64	mA
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		T_A = 25°C			SN54ABT541B		SN74ABT541B		UNIT
			MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}	V_{CC} = 4.5 V, I_I = –18 mA				–1.2		–1.2		–1.2	V
V_{OH}	V_{CC} = 4.5 V, I_{OH} = –3 mA		2.5			2.5		2.5		V
	V_{CC} = 5 V, I_{OH} = –3 mA		3			3		3		
	V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
		I_{OH} = –32 mA	2*					2		
V_{OL}	V_{CC} = 4.5 V	I_{OL} = 48 mA			0.55		0.55			V
		I_{OL} = 64 mA			0.55*				0.55	
I_I	V_{CC} = 5.5 V, V_I = V_{CC} or GND				±1		±1		±1	µA
I_{OZPU}	V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50		±50		±50	µA
I_{OZPD}	V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = X				±50		±50		±50	µA
I_{OZH}	V_{CC} = 5.5 V, V_O = 2.7 V				10		10		10	µA
I_{OZL}	V_{CC} = 5.5 V, V_O = 0.5 V				–10		–10		–10	µA
I_{off}	V_{CC} = 0, V_I or V_O ≤ 4.5 V				±100				±100	µA
I_{CEX}	V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O‡	V_{CC} = 5.5 V, V_O = 2.5 V		–50	–140	–180	–50	–180	–50	–180	mA
I_{CC}	V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		5	250		250		250	µA
		Outputs low		22	30		30		30	mA
		Outputs disabled		1	250		250		250	µA
ΔI_{CC}§	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND	Outputs enabled			1.5		1.5		1.5	mA
		Outputs disabled			50		50		50	µA
		Control inputs			1.5		1.5		1.5	mA
C_i	V_I = 2.5 V or 0.5 V			3						pF
C_o	V_O = 2.5 V or 0.5 V			6						pF

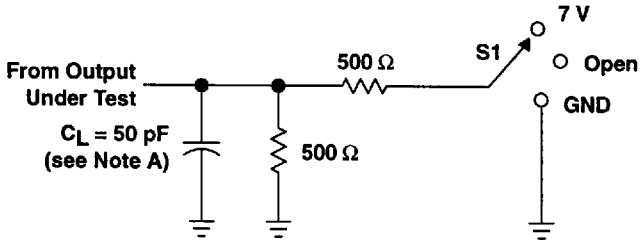
* On products compliant to MIL-STD-883, Class B, this parameter does not apply.
† All typical values are at V_{CC} = 5 V.
‡ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, T_A = 25°C			SN54ABT541B		SN74ABT541B		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	Y	1	2	3.2	1	3.8	1	3.6	ns
t_{PHL}			1	2.6	3.5	1	4.2	1	3.9	
t_{PZH}	$\overline{OE}$	Y	2	3.5	4.5	2	6	2	4	ns
t_{PZL}			1.9	4	5.1	1.9	6.5	1.9	5.9	
t_{PHZ}	$\overline{OE}$	Y	2.2	4.4	5.4	2.2	6	2.2	5.8	ns
t_{PLZ}			1.5	3	4	1.5	4.8	1.5	4.4	
$t_{sk(o)}$¶					0.5				0.5	ns

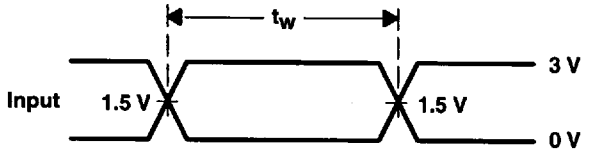
¶ Skew between any two outputs of the same package switching in the same direction. This parameter is specified by design.

PARAMETER MEASUREMENT INFORMATION

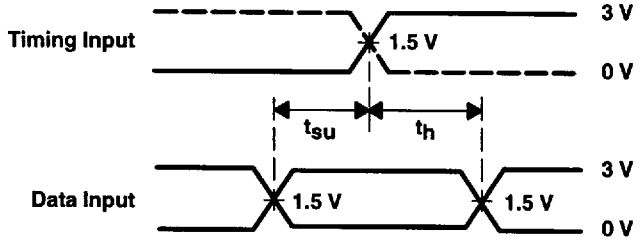


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

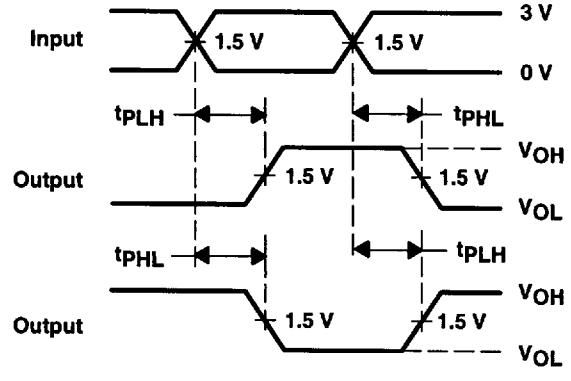
LOAD CIRCUIT



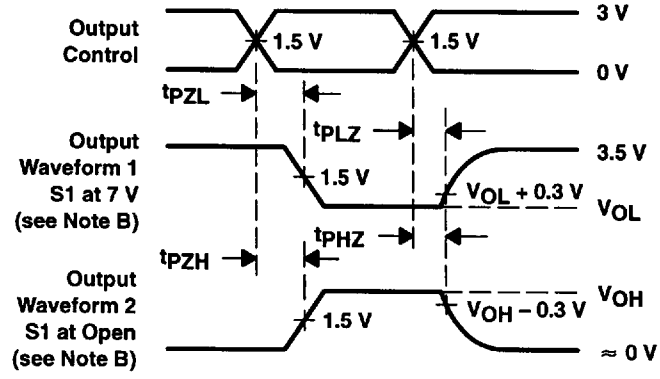
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms